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[DE/BE]; Herbert Hooverplein 20, B-3000 Leuven (BE).  
**CLAES, Martine** [BE/BE]; Oude Baan 21, B-3060  
Bertem (BE).

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(74) Agent: **KONTRUS, Gerhard**; c/o SEZ AG, Draubodenweg 29, A-9500 Villach (AT).

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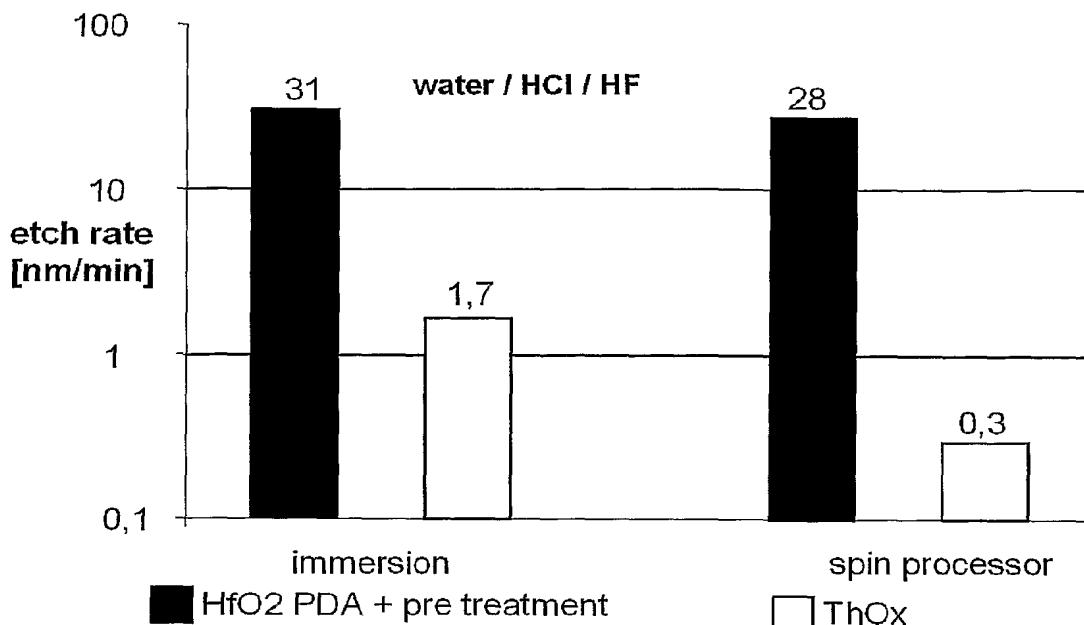
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(71) Applicants (for all designated States except US): **SEZ AG** [AT/AT]; Draubodenweg 29, A-9500 Villach (AT). **INTERUNIVERSITAIR MICRO-ELEKTRONICA CENTRUM VZW** [BE/BE]; Kapeldreef 75, B-3001 Lueven (BE).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **KRAUS, Harald**

(54) Title: METHOD FOR SELECTIVE ETCHING



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(57) Abstract: Disclosed is a method of selective etching a first material on a substrate with a high selectivity towards a second material by flowing a liquid etchant across a substrate surface at a flow sufficient fast to generate a minimum mean velocity  $v$  parallel to the substrate's surface.



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